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(54) Title: POST-LAPPING CLEANING PROCESS FOR SILICON WAFERS

(57) Abstract

A process for cleaning contaminants from the surface of a semiconductor wafer after the wafer has been lapped. The process comprises contacting the wafer with an oxidizing agent to oxidize organic contaminants which may be present on the surface of the wafer. The wafer is then immersed in an aqueous bath comprising citric acid into which sonic energy is being directed to remove metallic contaminants which may be present on the surface of the wafer. After being immersed in the citric acid bath, the wafer is contacted with hydrofluoric acid to remove a layer of silicon dioxide which may be present on the surface of the wafer. The wafer is then immersed in an aqueous bath comprising an alkaline component and a surfactant, and into which sonic energy is being directed.